IGBT

High speed 5 FAST IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft anti parallel diode

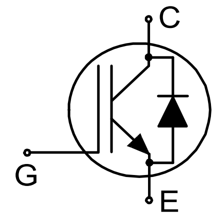
IKP08N65F5

650V DuoPack IGBT and Diode
High speed switching series fifth generation

Data sheet

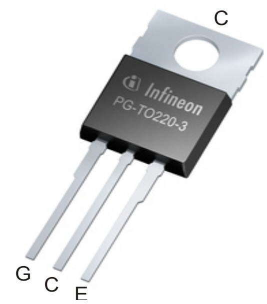
Industrial Power Control

High speed 5 FAST IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft anti parallel diode



Features and Benefits:

High speed F5 technology offering
- Best-in-Class efficiency in hard switching and resonant topologies
- 650V breakdown voltage
- Low Q_g
- IGBT copacked with RAPID 1 fast and soft antiparallel diode
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/



Applications:

- Solar converters
- Uninterruptible power supplies
- Welding converters
- Mid to high range switching frequency converters

Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
IKP08N65F5	650V	8A	1.6V	175°C	K08F655	PG-TO220-3

Table of Contents

Description . . . 2
Table of Contents . . . 3
Maximum ratings . . . 4
Thermal Resistance . . . 4
Electrical Characteristics . . . 5
Electrical Characteristics diagrams . . . 8
Package Drawing . . . 15
Testing Conditions . . . 16
Revision History . . . 17
Disclaimer . . . 17

Maximum ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	650	V
DC collector current, limited by T_{vjmax} T_C = 25°C T_C = 100°C	I_C	18.0 11.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	24.0	A
Turn off safe operating area $V_{CE} \leq$ 650V, $T_{vj} \leq$ 175°C	-	24.0	A
Diode forward current, limited by T_{vjmax} T_C = 25°C T_C = 100°C	I_F	20.0 12.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	24.0	A
Gate-emitter voltage Transient Gate-emitter voltage (t_p = 10µs, D < 0.010)	V_{GE}	±20 ±30	V
Power dissipation T_C = 25°C Power dissipation T_C = 100°C	P_{tot}	70.0 31.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s		260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		2.20	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		2.90	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		62	K/W

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value min.	Value typ.	Value max.	Unit
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0V, I_C = 0.20mA	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	V_{GE} = 15.0V, I_C = 8.0A T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 175°C	- - -	1.60 1.80 1.90	2.10 - -	V
Diode forward voltage	V_F	V_{GE} = 0V, I_F = 9.0A T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 175°C	- - -	1.45 1.40 1.40	1.80 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 0.08mA, V_{CE} = V_{GE}	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 650V, V_{GE} = 0V T_{vj} = 25°C T_{vj} = 175°C	- -	- -	40.0 4000.0	µA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0V, V_{GE} = 20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE} = 20V, I_C = 8.0A	-	17.0	-	S

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value min.	Value typ.	Value max.	Unit
Dynamic Characteristic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	500	-	pF
Output capacitance	C_{oes}		-	16	-	
Reverse transfer capacitance	C_{res}		-	3	-	
Gate charge	Q_G	V_{CC} = 520V, I_C = 8.0A, V_{GE} = 15V	-	22.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7.0	-	nH

Switching Characteristic, Inductive Load, at T_{vj} = 25°C

Parameter	Symbol	Conditions	Value min.	Value typ.	Value max.	Unit
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 4.0A, V_{GE} = 0.0/15.0V, r_G = 48.0Ω, $L\sigma$ = 30nH, $C\sigma$ = 30pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	10	-	ns
Rise time	t_r		-	5	-	ns
Turn-off delay time	$t_{d(off)}$		-	116	-	ns
Fall time	t_f		-	20	-	ns
Turn-on energy	E_{on}		-	0.07	-	mJ
Turn-off energy	E_{off}		-	0.02	-	mJ
Total switching energy	E_{ts}		-	0.09	-	mJ

Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 2.0A, V_{GE} = 0.0/15.0V, r_G = 48.0Ω, $L\sigma$ = 30nH, $C\sigma$ = 30pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	9	-	ns
Rise time	t_r		-	3	-	ns
Turn-off delay time	$t_{d(off)}$		-	129	-	ns
Fall time	t_f		-	35	-	ns
Turn-on energy	E_{on}		-	0.04	-	mJ
Turn-off energy	E_{off}		-	0.02	-	mJ
Total switching energy	E_{ts}		-	0.06	-	mJ

Diode Characteristic, at T_{vj} = 25°C

Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 4.0A, di_F/dt = 800A/µs	-	41	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.14	-	µC
Diode peak reverse recovery current	I_{rrm}		-	6.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-160	-	A/µs
Diode reverse recovery time	t_{rr}	T_{vj} = 25°C, V_R = 400V, I_F = 2.0A, di_F/dt = 800A/µs	-	27	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.10	-	µC
Diode peak reverse recovery current	I_{rrm}		-	6.2	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-300	-	A/µs

Switching Characteristic, Inductive Load, at T_{vj} = 150°C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 150°C, V_{CC} = 400V, I_C = 4.0A, V_{GE} = 0.0/15.0V, r_G = 48.0Ω, $L\sigma$ = 30nH, $C\sigma$ = 30pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	9	-	ns
Rise time	t_r		-	6	-	ns
Turn-off delay time	$t_{d(off)}$		-	145	-	ns
Fall time	t_f		-	18	-	ns
Turn-on energy	E_{on}		-	0.10	-	mJ
Turn-off energy	E_{off}		-	0.03	-	mJ
Total switching energy	E_{ts}		-	0.13	-	mJ
Turn-on delay time	$t_{d(on)}$	T_{vj} = 150°C, V_{CC} = 400V, I_C = 2.0A, V_{GE} = 0.0/15.0V, r_G = 48.0Ω, $L\sigma$ = 30nH, $C\sigma$ = 30pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	9	-	ns
Rise time	t_r		-	4	-	ns
Turn-off delay time	$t_{d(off)}$		-	165	-	ns
Fall time	t_f		-	25	-	ns
Turn-on energy	E_{on}		-	0.06	-	mJ
Turn-off energy	E_{off}		-	0.02	-	mJ
Total switching energy	E_{ts}		-	0.08	-	mJ

Diode Characteristic, at T_{vj} = 150°C

Diode reverse recovery time	t_{rr}	T_{vj} = 150°C, V_R = 400V, I_F = 4.0A, di_F/dt = 800A/µs	-	56	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.27	-	µC
Diode peak reverse recovery current	I_{rrm}		-	7.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-134	-	A/µs

Diode reverse recovery time	t_{rr}	T_{vj} = 150°C, V_R = 400V, I_F = 2.0A, di_F/dt = 800A/µs	-	42	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.19	-	µC
Diode peak reverse recovery current	I_{rrm}		-	7.4	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-240	-	A/µs

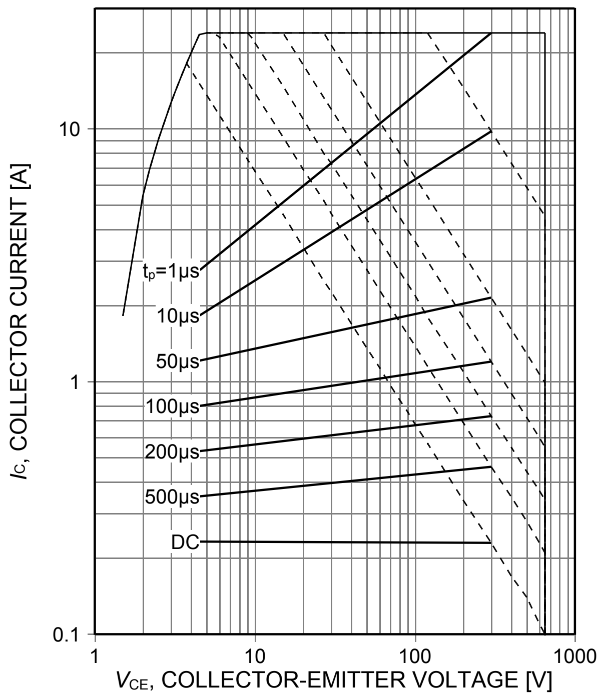


Figure 1. **Forward bias safe operating area**
(D=0, T_C=25°C, T_{vj}≤175°C; V_{GE}=15V. Recommended use at V_{GE}≥7.5V)

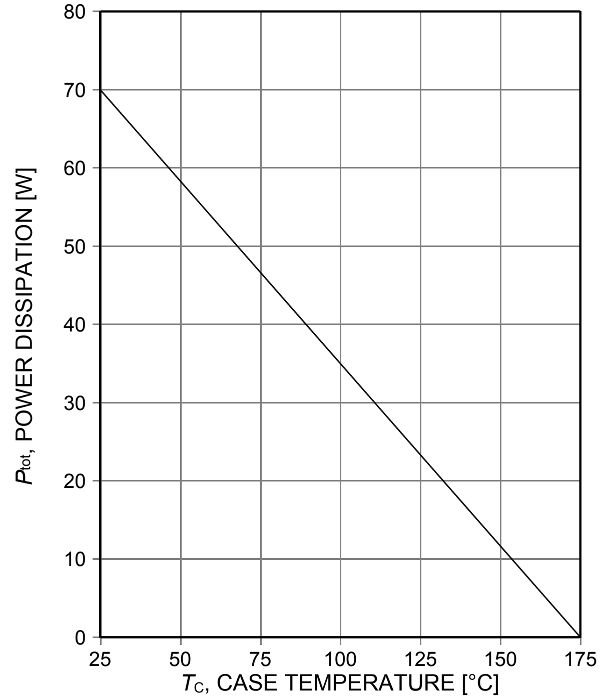


Figure 2. **Power dissipation as a function of case temperature**
(T_{vj}≤175°C)

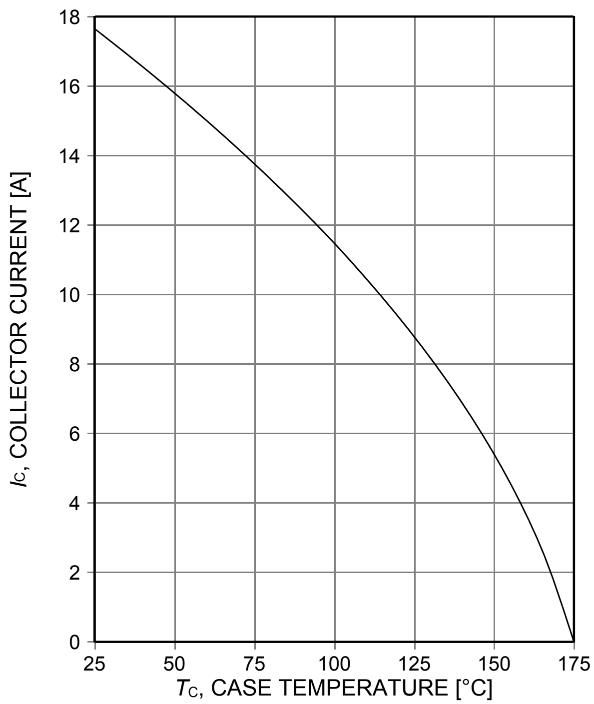


Figure 3. **Collector current as a function of case temperature**
(V_{GE}≥15V, T_{vj}≤175°C)

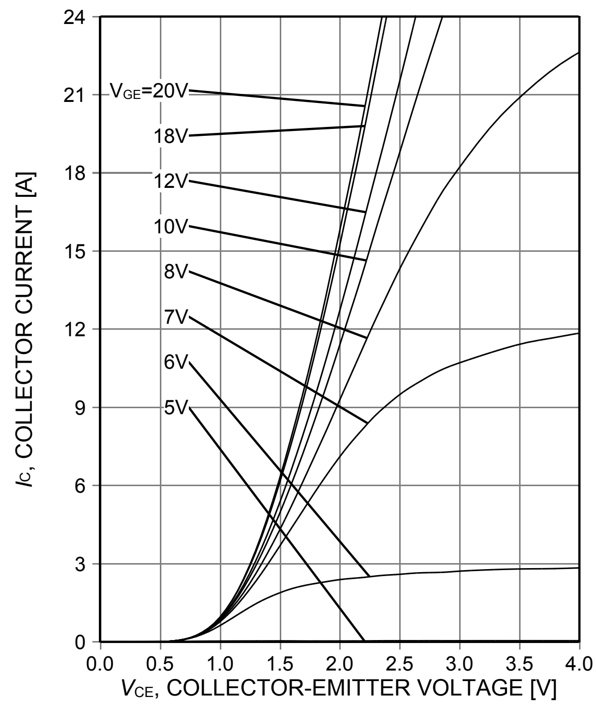


Figure 4. **Typical output characteristic**
(T_{vj}=25°C)

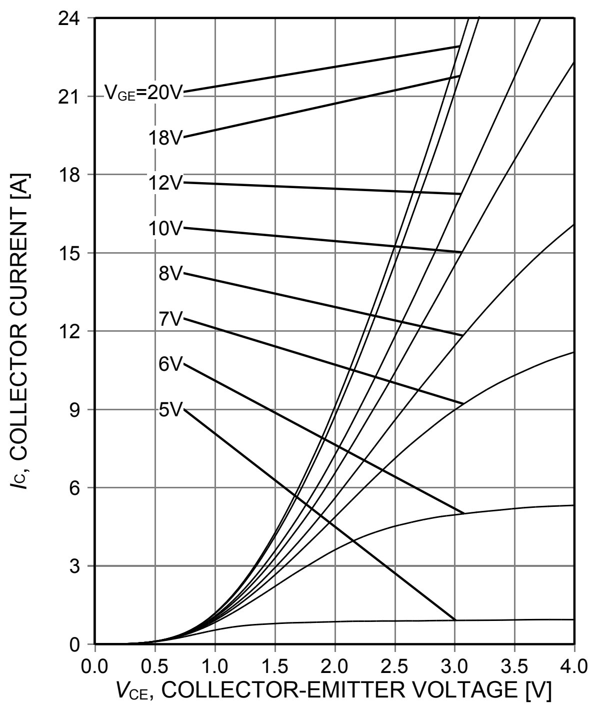


Figure 5. **Typical output characteristic**
(T_{vj}=150°C)

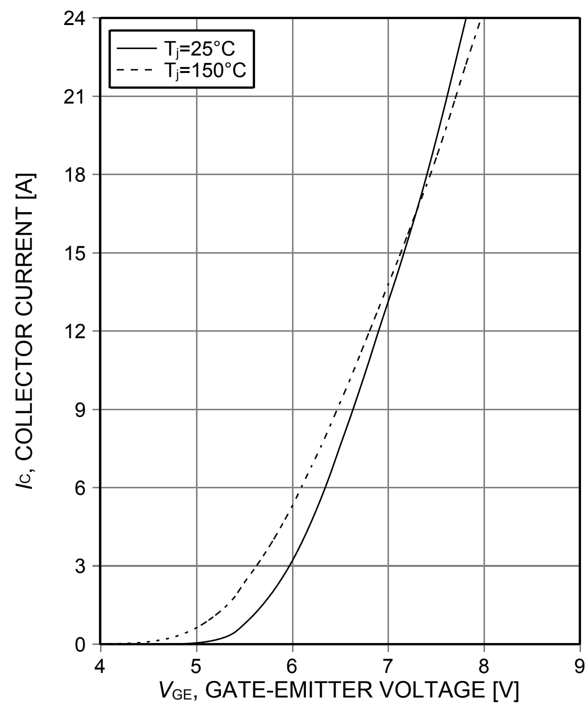


Figure 6. **Typical transfer characteristic**
(V_{CE}=20V)

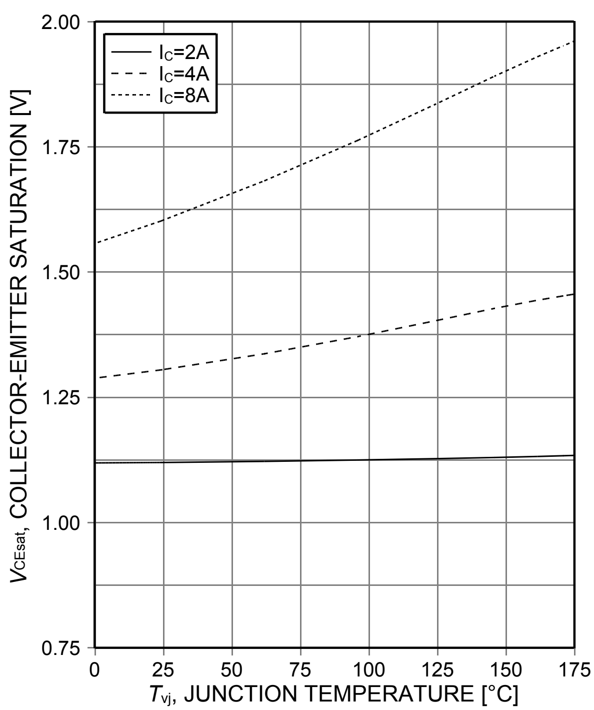


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**
(V_{GE}=15V)

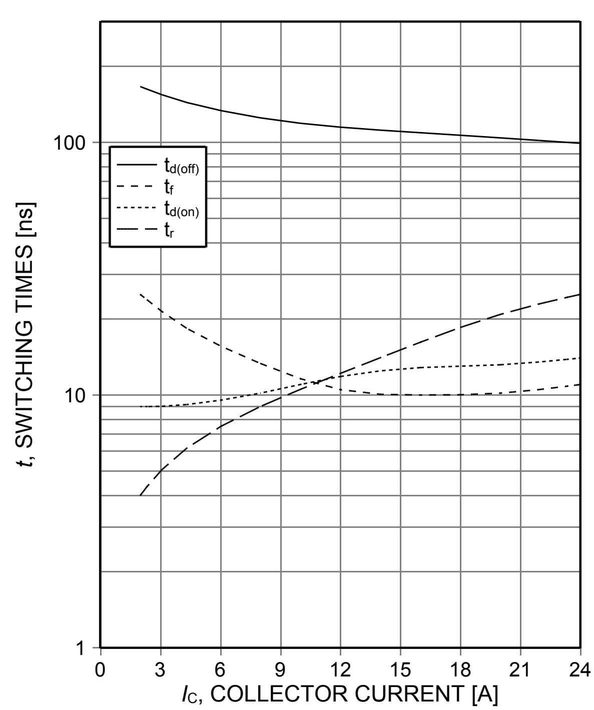


Figure 8. **Typical switching times as a function of collector current**
(inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, r_G=48Ω, Dynamic test circuit in Figure E)

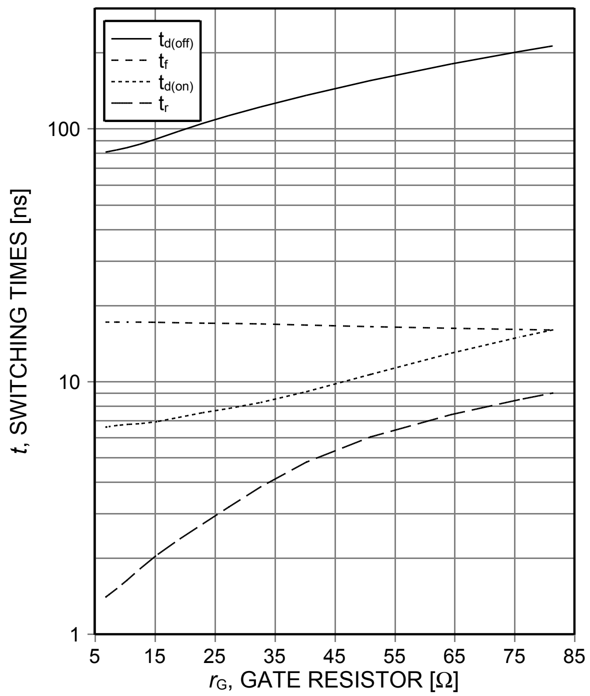


Figure 9. **Typical switching times as a function of gate resistor**
(inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, I_C=4A,Dynamic test circuit in Figure E)

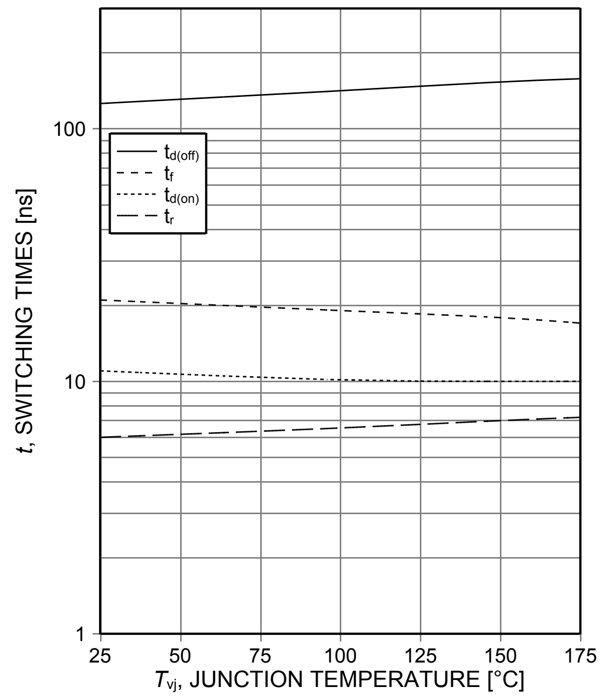


Figure 10. **Typical switching times as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=15/0V, I_C=4A, r_G=48Ω,Dynamic test circuit in Figure E)

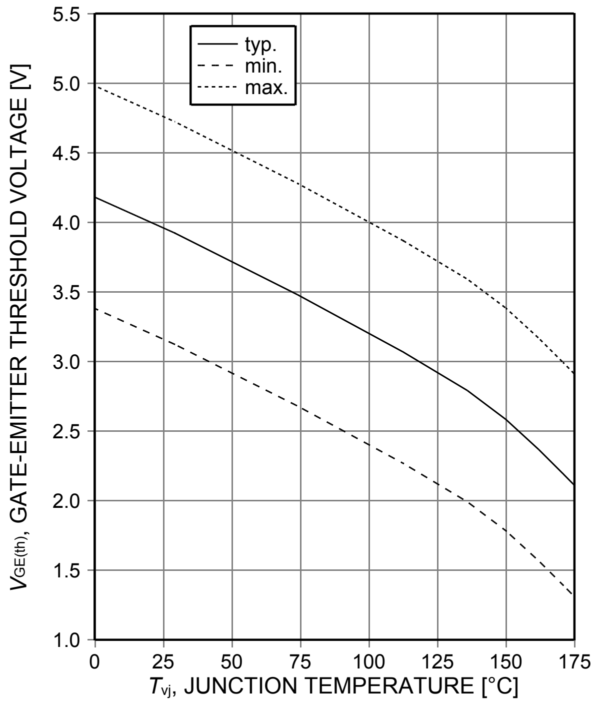


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**
(I_C=0.08mA)

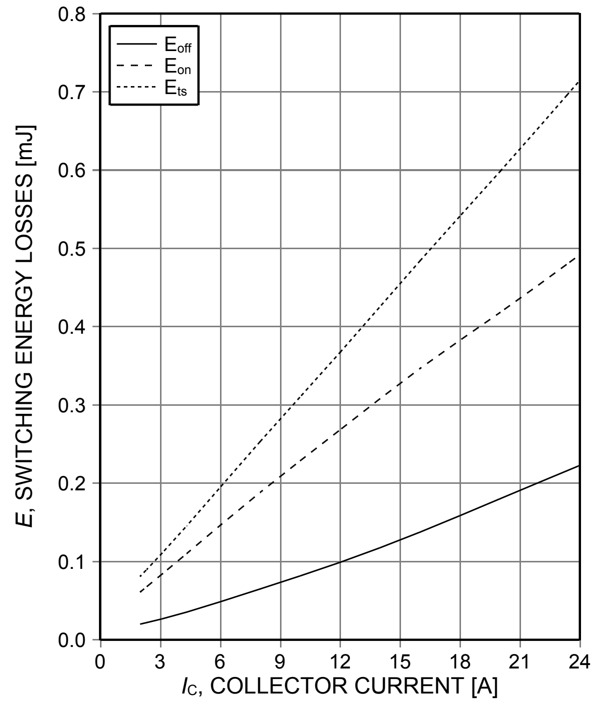


Figure 12. **Typical switching energy losses as a function of collector current**
(inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, r_G=48Ω,Dynamic test circuit in Figure E)

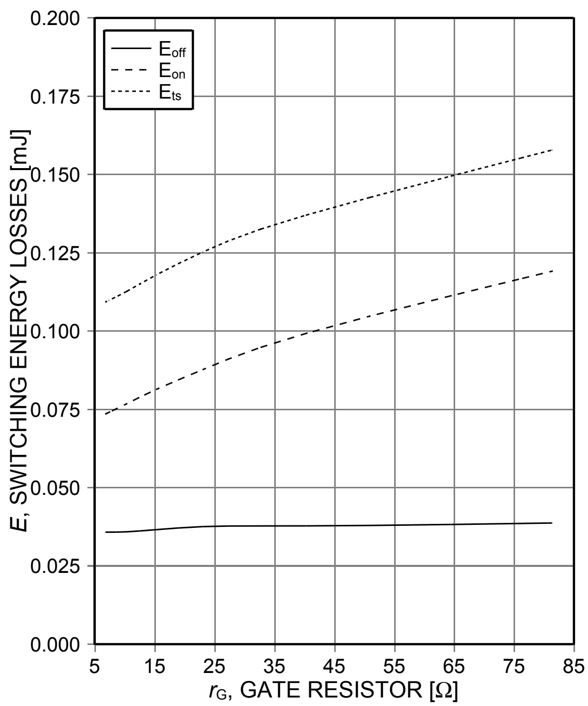


Figure 13. **Typical switching energy losses as a function of gate resistor**
(inductive load, T_{vj}=150°C, V_{CE}=400V, V_{GE}=15/0V, I_C=4A, Dynamic test circuit in Figure E)

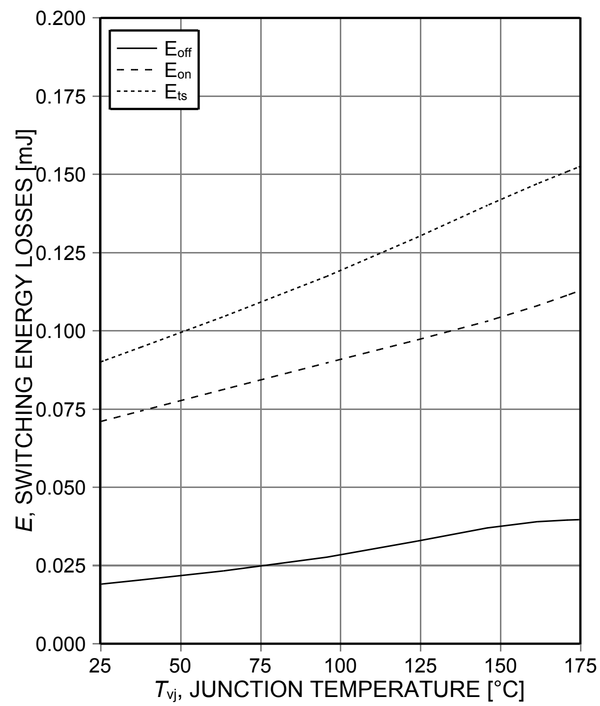


Figure 14. **Typical switching energy losses as a function of junction temperature**
(inductive load, V_{CE}=400V, V_{GE}=15/0V, I_C=4A, r_G=48Ω,Dynamic test circuit in Figure E)

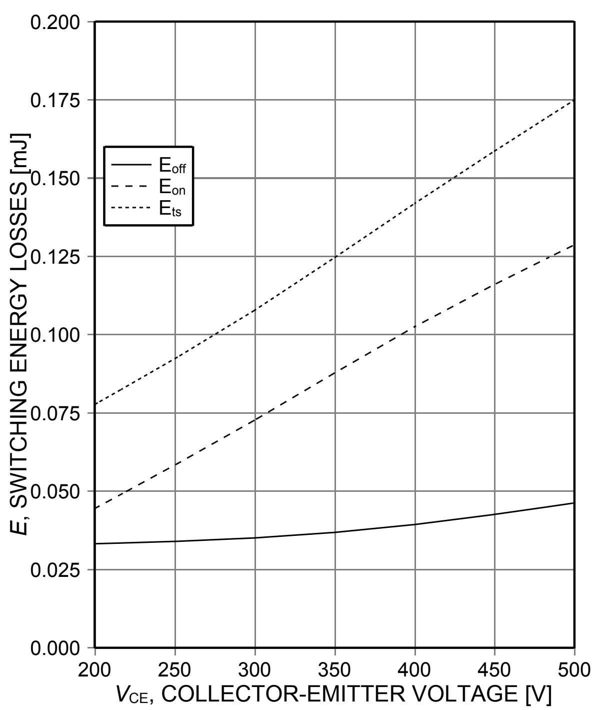


Figure 15. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, T_{vj}=150°C, V_{GE}=15/0V, I_C=4A, r_G=48Ω,Dynamic test circuit in Figure E)

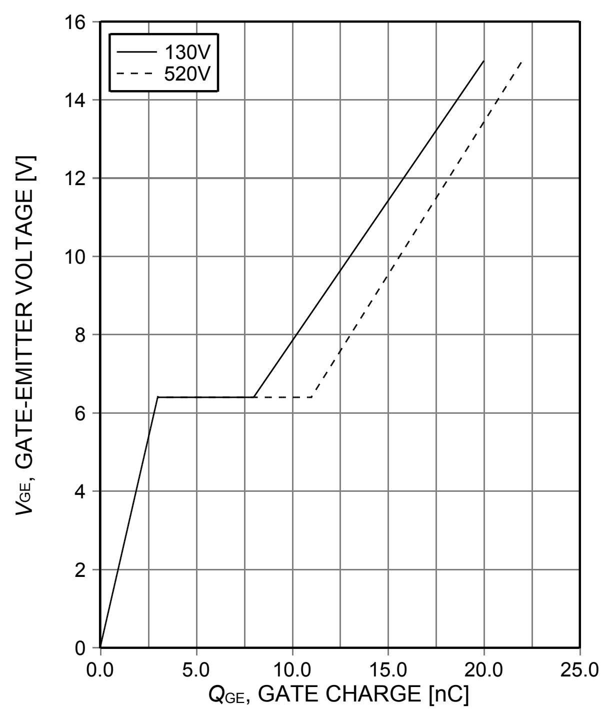


Figure 16. **Typical gate charge**
(I_C=8A)

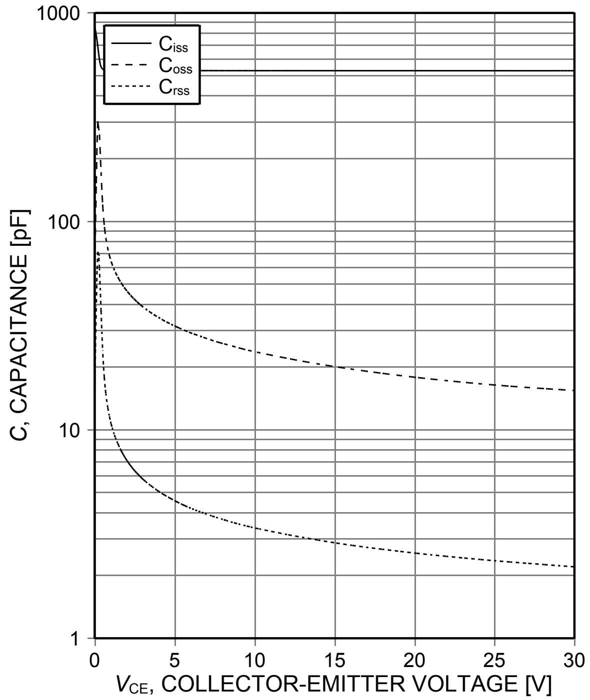


Figure 17. **Typical capacitance as a function of collector-emitter voltage**
(V_{GE}=0V, f=1MHz)

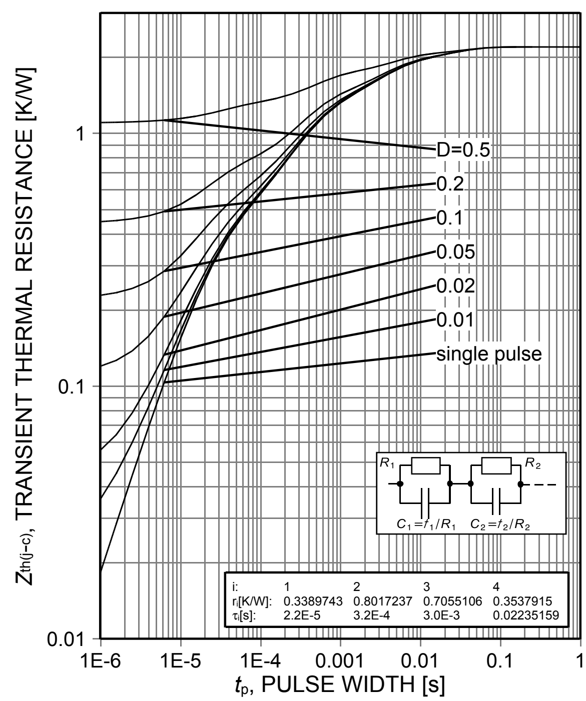


Figure 18. **IGBT transient thermal resistance**
(D=t_p/T)

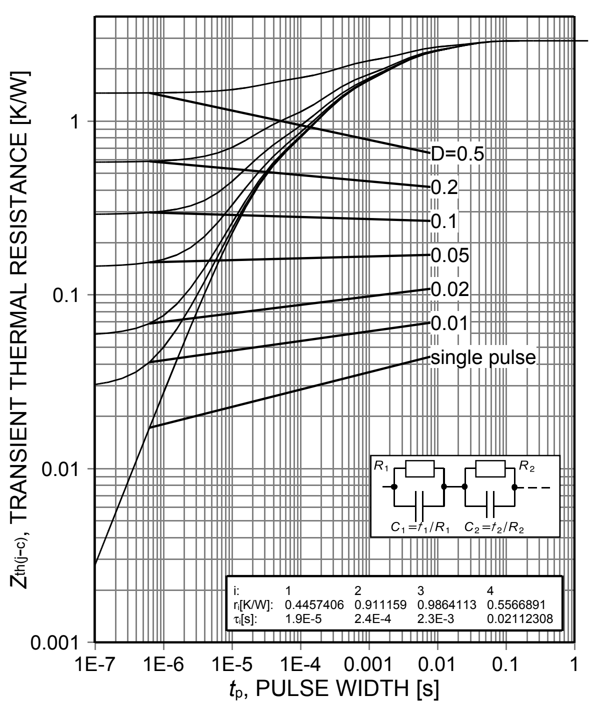


Figure 19. **Diode transient thermal impedance as a function of pulse width**
(D=t_p/T)

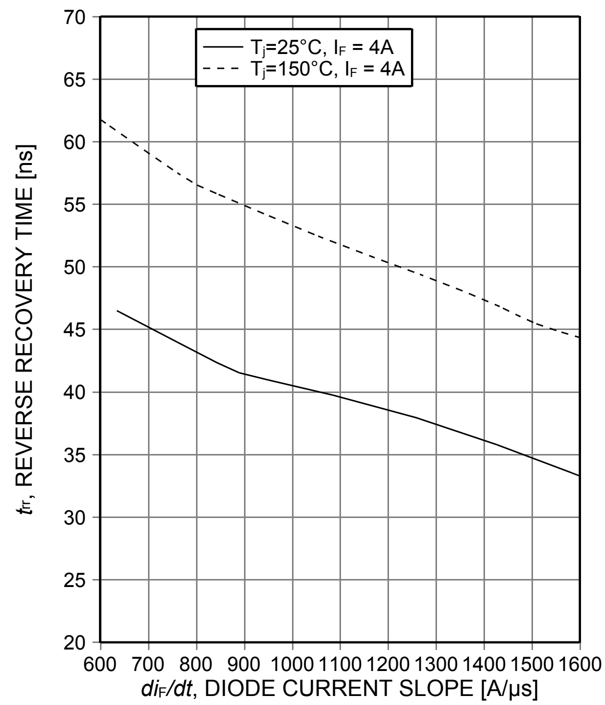


Figure 20. **Typical reverse recovery time as a function of diode current slope**
(V_R=400V)

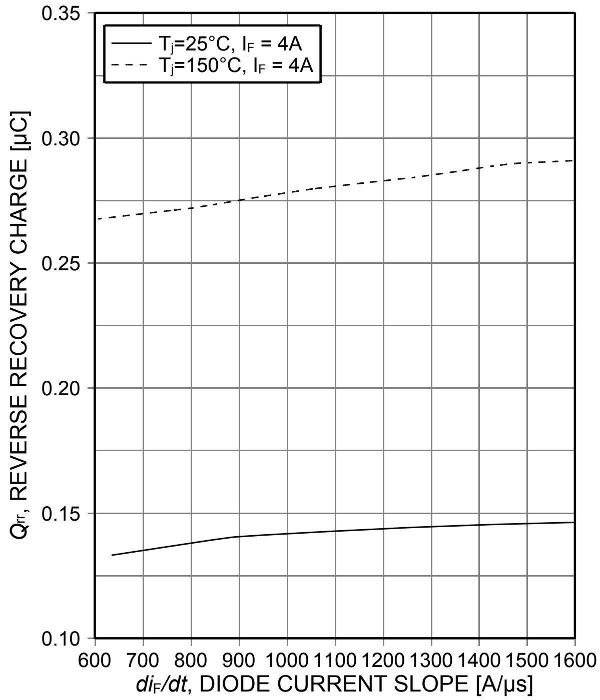


Figure 21. **Typical reverse recovery charge as a function of diode current slope**
(V_R=400V)

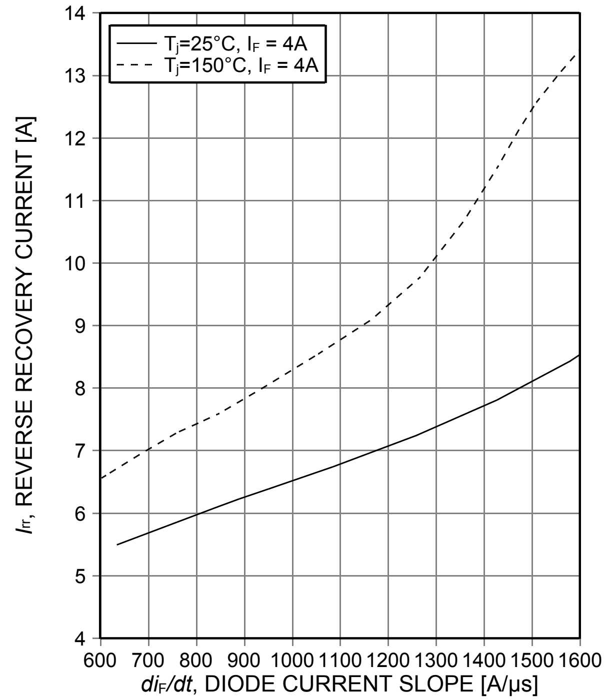


Figure 22. **Typical reverse recovery current as a function of diode current slope**
(V_R=400V)

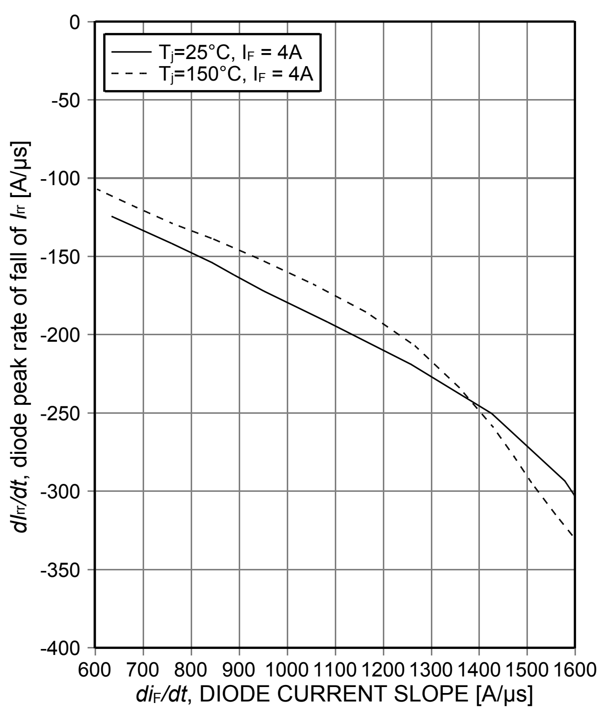


Figure 23. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
(V_R=400V)

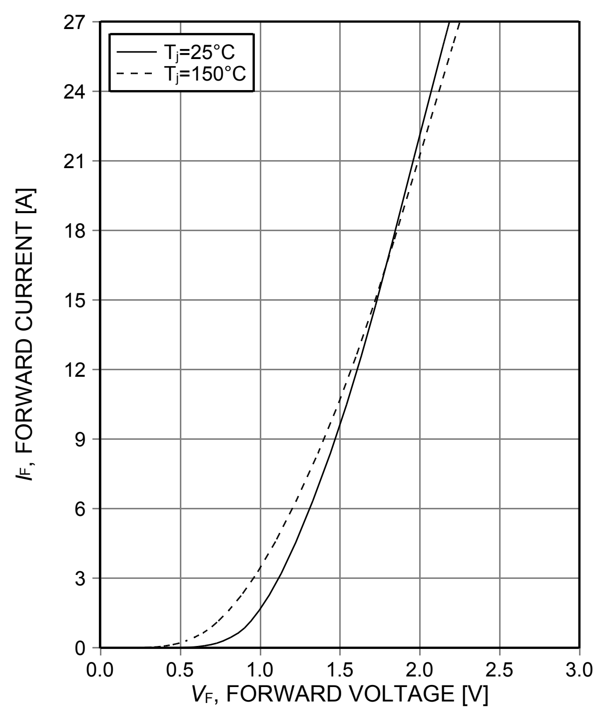


Figure 24. **Typical diode forward current as a function of forward voltage**

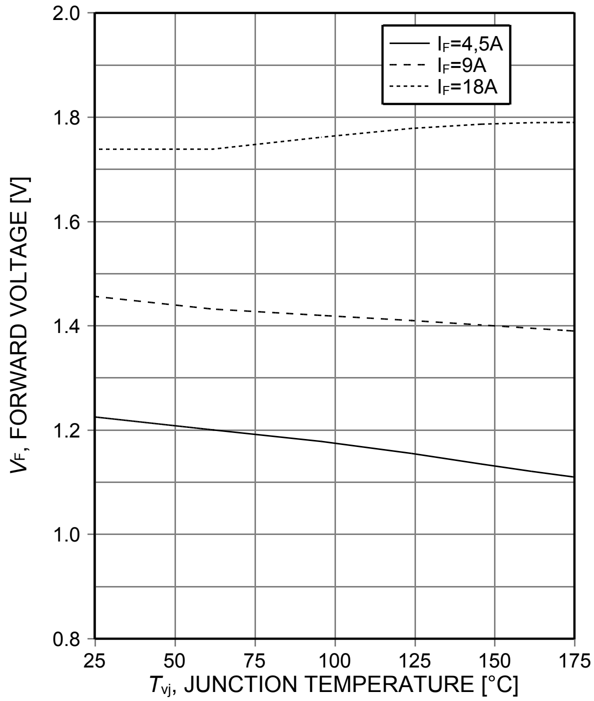
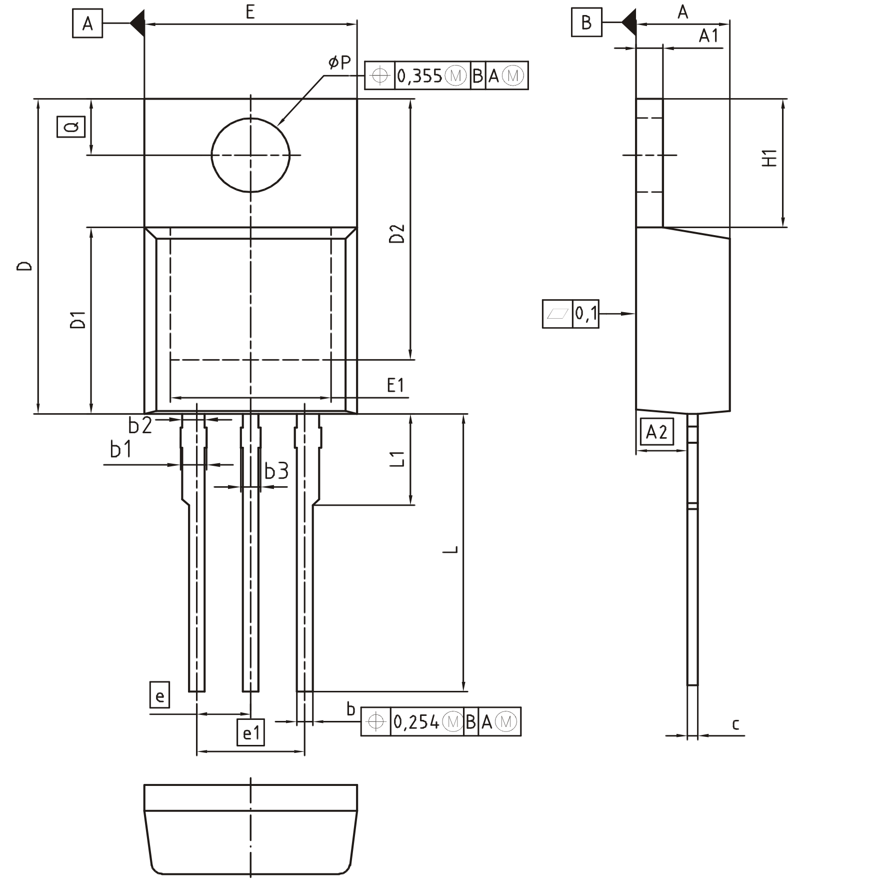


Figure 25. **Typical diode forward voltage as a function of junction temperature**

PG-TO220-3

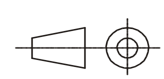


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00003318

SCALE 0 2.5 5mm

EUROPEAN PROJECTION



ISSUE DATE
30-07-2009

REVISION
06

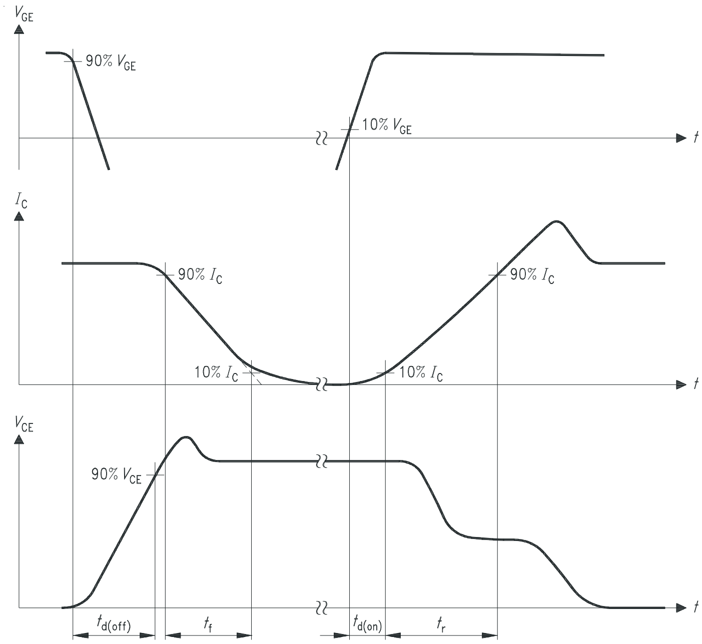


Figure A. Definition of switching times

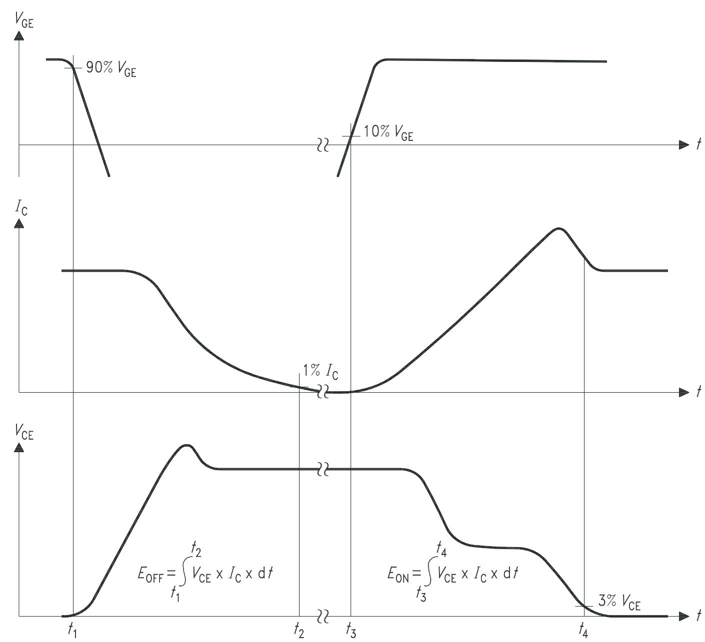


Figure B. Definition of switching losses

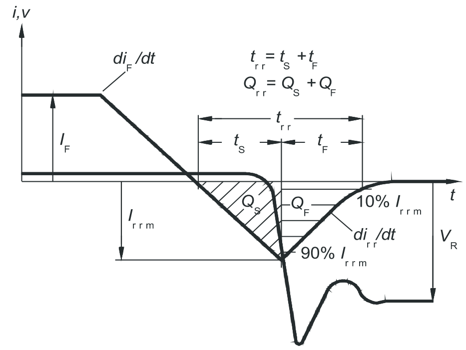


Figure C. Definition of diodes switching characteristics

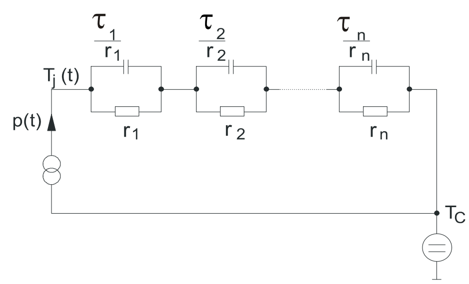


Figure D. Thermal equivalent circuit

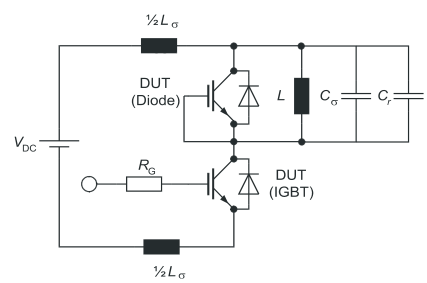


Figure E. Dynamic test circuit

Parasitic inductance L_σ ,
Parasitic capacitor C_σ ,
Relief capacitor C_r
(only for ZVT switching)

Revision History

IKP08N65F5

Revision: 2012-11-09, Rev. 1.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.1	2012-11-09	Preliminary data sheet

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